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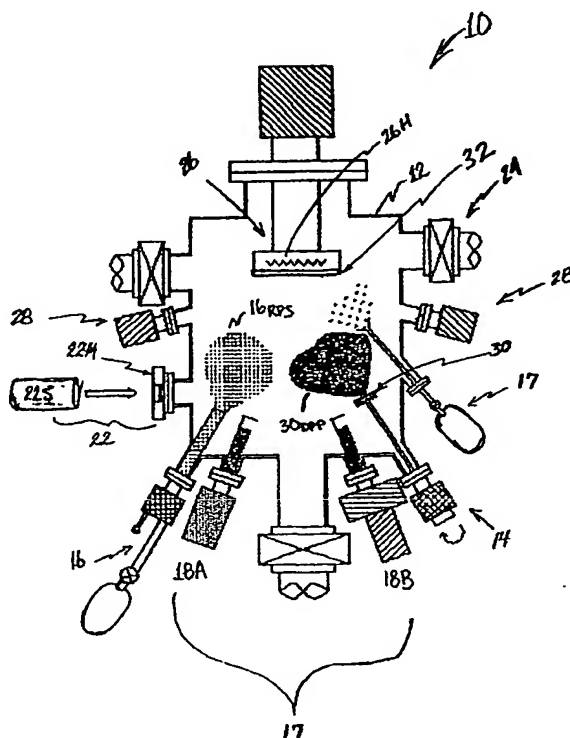
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(54) Title: A HYBRID BEAM DEPOSITION SYSTEM AND METHODS FOR FABRICATING METAL OXIDE ZNO FILMS,
P-TYPE ZNO FILMS, AND ZNO-BASED II-VI COMPOUND SEMICONDUCTOR DEVICES



(57) Abstract: A hybrid beam deposition (HBD) system and methods according to the present invention utilizes a unique combination of pulsed laser deposition (PLD) technique and equipment with equipment and techniques that provide a radical oxygen rf-plasma stream to effectively increase the flux density of available reactive oxygen at a deposition substrate for the effective synthesis of metal oxide thin films. The HBD system and methods of the present invention further integrate molecular beam epitaxy (MBE) and/or chemical vapor deposition (CVD) techniques and equipment in combination with the PLD equipment and technique and the radical oxygen rf-plasma stream to provide elemental source materials for the synthesis of undoped and/or doped metal oxide thin films as well as the synthesis of undoped and/or doped metal-based oxide alloy thin films.

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